

HEF4069UB

Hex inverter

Rev. 06 — 8 December 2009

Product data sheet

1. General description

The HEF4069UB is a general purpose hex inverter. Each inverter has a single stage.

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD} , V_{SS} , or another input.

It is also suitable for use over both the industrial ($-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$) and automotive ($-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$) temperature ranges.

2. Features

- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- Operates across the automotive temperature range from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Complies with JEDEC standard JESD 13-B

3. Applications

- Automotive and industrial
- Oscillator

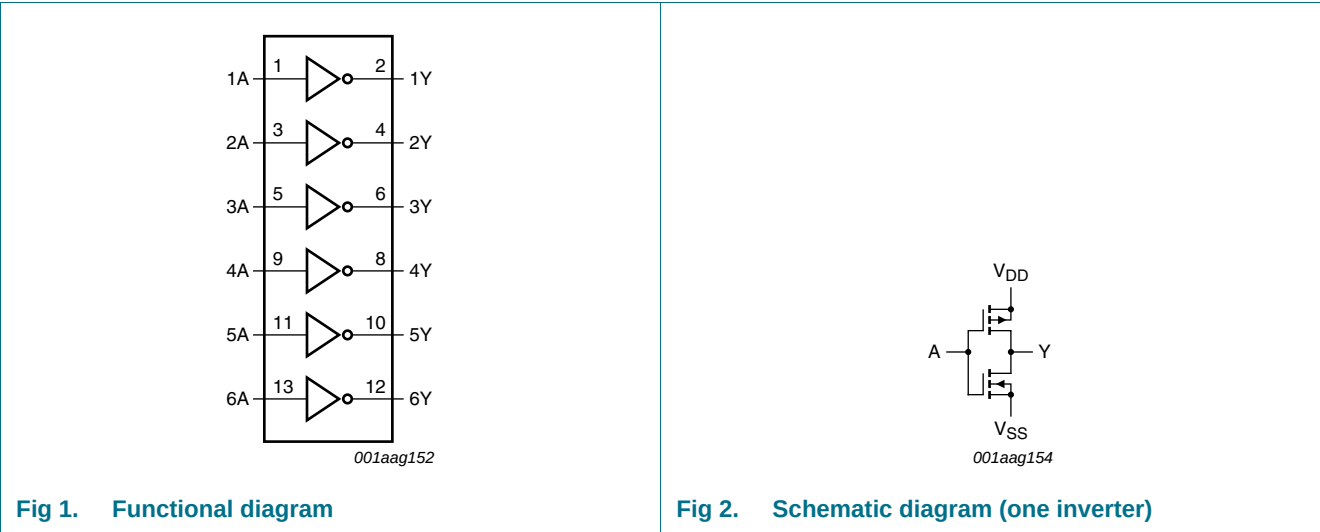
4. Ordering information

Table 1. Ordering information

All types operate from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$.

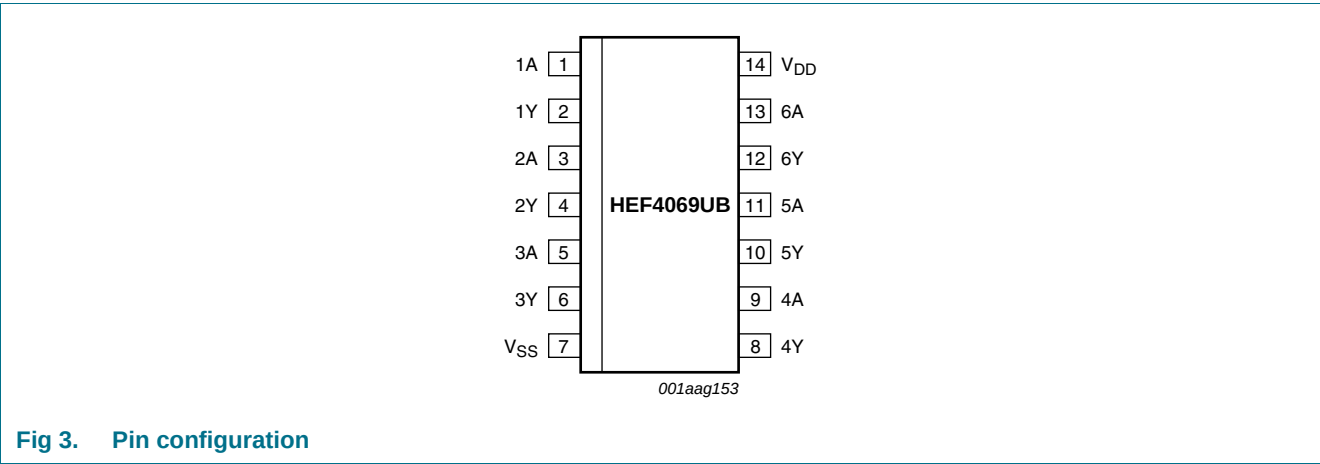
Type number	Package		
	Name	Description	Version
HEF4069UBP	DIP14	plastic dual in-line package; 14 leads (300 mil)	SOT27-1
HEF4069UBT	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
HEF4069UBTT	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Symbol	Pin	Description
1A to 6A	1, 3, 5, 9, 11, 13	input
1Y to 6Y	2, 4, 6, 8, 10, 12	output
V _{SS}	7	ground (0 V)
V _{DD}	14	supply voltage

7. Limiting values

Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		-0.5	+18	V
I_{IK}	input clamping current	$V_I < -0.5 \text{ V}$ or $V_I > V_{DD} + 0.5 \text{ V}$	-	± 10	mA
V_I	input voltage		-0.5	$V_{DD} + 0.5$	V
I_{OK}	output clamping current	$V_O < -0.5 \text{ V}$ or $V_O > V_{DD} + 0.5 \text{ V}$	-	± 10	mA
$I_{I/O}$	input/output current		-	± 10	mA
I_{DD}	supply current		-	50	mA
T_{stg}	storage temperature		-65	+150	°C
T_{amb}	ambient temperature		-40	+125	°C
P_{tot}	total power dissipation	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$			
		DIP14	[1] -	750	mW
		SO14	[2] -	500	mW
		TSSOP14	[3] -	500	mW
P	power dissipation	per output	-	100	mW

[1] For DIP14 packages: above $T_{amb} = 70 \text{ °C}$, P_{tot} derates linearly with 12 mW/K.

[2] For SO14 packages: above $T_{amb} = 70 \text{ °C}$, P_{tot} derates linearly with 8 mW/K.

[3] For TSSOP14 packages: above $T_{amb} = 60 \text{ °C}$, P_{tot} derates linearly with 5.5 mW/K.

8. Recommended operating conditions

Table 4. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DD}	supply voltage		3	-	15	V
V_I	input voltage		0	-	V_{DD}	V
T_{amb}	ambient temperature	in free air	-40	-	+125	°C

9. Static characteristics

Table 5. Static characteristics

$V_{SS} = 0\text{ V}$; $V_I = V_{SS}$ or V_{DD} ; unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	$T_{amb} = -40\text{ °C}$		$T_{amb} = +25\text{ °C}$		$T_{amb} = +85\text{ °C}$		$T_{amb} = +125\text{ °C}$		Unit
				Min	Max	Min	Max	Min	Max	Min	Max	
V_{IH}	HIGH-level input voltage	$ I_O < 1\text{ }\mu\text{A}$	5 V	4	-	4	-	4	-	4	-	V
			10 V	8	-	8	-	8	-	8	-	V
			15 V	12.5	-	12.5	-	12.5	-	12.5	-	V
V_{IL}	LOW-level input voltage	$ I_O < 1\text{ }\mu\text{A}$	5 V	-	1	-	1	-	1	-	1	V
			10 V	-	2	-	2	-	2	-	2	V
			15 V	-	2.5	-	2.5	-	2.5	-	2.5	V
V_{OH}	HIGH-level output voltage	$ I_O < 1\text{ }\mu\text{A}$	5 V	4.95	-	4.95	-	4.95	-	4.95	-	V
			10 V	9.95	-	9.95	-	9.95	-	9.95	-	V
			15 V	14.95	-	14.95	-	14.95	-	14.95	-	V
V_{OL}	LOW-level output voltage	$ I_O < 1\text{ }\mu\text{A}$	5 V	-	0.05	-	0.05	-	0.05	-	0.05	V
			10 V	-	0.05	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	-	0.05	V
I_{OH}	HIGH-level output current	$V_O = 2.5\text{ V}$	5 V	-1.7	-	-1.4	-	-1.1	-	-1.1	-	mA
		$V_O = 4.6\text{ V}$	5 V	-0.64	-	-0.5	-	-0.36	-	-0.36	-	mA
		$V_O = 9.5\text{ V}$	10 V	-1.6	-	-1.3	-	-0.9	-	-0.9	-	mA
		$V_O = 13.5\text{ V}$	15 V	-4.2	-	-3.4	-	-2.4	-	-2.4	-	mA
I_{OL}	LOW-level output current	$V_O = 0.4\text{ V}$	5 V	0.64	-	0.5	-	0.36	-	0.36	-	mA
		$V_O = 0.5\text{ V}$	10 V	1.6	-	1.3	-	0.9	-	0.9	-	mA
		$V_O = 1.5\text{ V}$	15 V	4.2	-	3.4	-	2.4	-	2.4	-	mA
I_I	input leakage current		15 V	-	± 0.1	-	± 0.1	-	± 1.0	-	± 1.0	μA
I_{DD}	supply current	all valid input combinations; $I_O = 0\text{ A}$	5 V	-	0.25	-	0.25	-	7.5	-	7.5	μA
			10 V	-	0.5	-	0.5	-	15.0	-	15.0	μA
			15 V	-	1.0	-	1.0	-	30.0	-	30.0	μA
C_I	input capacitance	digital inputs		-	-	-	7.5	-	-	-	-	pF

10. Dynamic characteristics

Table 6. Dynamic characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$; for waveforms see [Figure 4](#); for test circuit see [Figure 5](#).

Symbol	Parameter	Conditions	V _{DD}	Extrapolation formula ^[1]	Min	Typ	Max	Unit
t _{PHL}	HIGH to LOW propagation delay	nA to nY;	5 V	18 ns + (0.55 ns/pF)C _L	-	45	90	ns
			10 V	9 ns + (0.23 ns/pF)C _L	-	20	40	ns
			15 V	7 ns + (0.16 ns/pF)C _L	-	15	25	ns
t _{PLH}	LOW to HIGH propagation delay	nA to nY	5 V	13 ns + (0.55 ns/pF)C _L	-	40	80	ns
			10 V	9 ns + (0.23 ns/pF)C _L	-	20	40	ns
			15 V	7 ns + (0.16 ns/pF)C _L	-	15	30	ns
t _{THL}	HIGH to LOW output transition time	output nY	5 V	10 ns + (1.0 0 ns/pF)C _L	-	60	120	ns
			10 V	9 ns + (0.42 ns/pF)C _L	-	30	60	ns
			15 V	6 ns + (0.28 ns/pF)C _L	-	20	40	ns
t _{TLH}	LOW to HIGH output transition time	output nY	5 V	10 ns + (1.00 ns/pF)C _L	-	60	120	ns
			10 V	9 ns + (0.42 ns/pF)C _L	-	30	60	ns
			15 V	6 ns + (0.28 ns/pF)C _L	-	20	40	ns

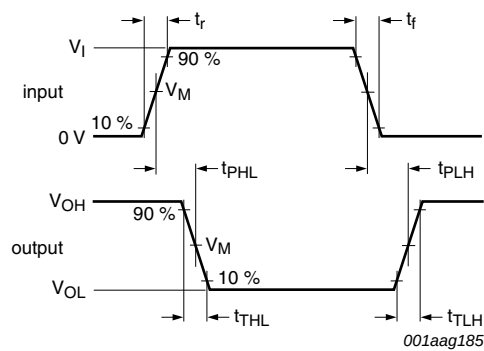
[1] The typical value of the propagation delay and output transition time can be calculated with the extrapolation formula (C_L in pF).

Table 7. Dynamic power dissipation

$V_{SS} = 0\text{ V}$; $t_r = t_f \leq 20\text{ ns}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

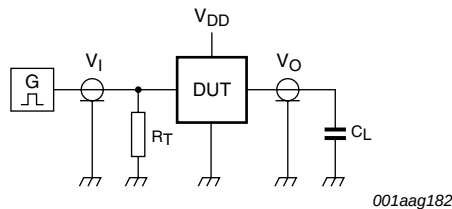
Symbol	Parameter	V _{DD}	Typical formula	Where
P _D	dynamic power dissipation	5 V	$P_D = 600 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$ (μW)	f _i = input frequency in MHz;
		10 V	$P_D = 4000 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$ (μW)	f _o = output frequency in MHz;
		15 V	$P_D = 22000 \times f_i + \Sigma(f_o \times C_L) \times V_{DD}^2$ (μW)	C _L = output load capacitance in pF; Σ(f _o × C _L) = sum of the outputs; V _{DD} = supply voltage in V.

11. Waveforms



Measurement points: $V_M = 0.5V_{DD}$.
Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 4. Propagation delay and transition times



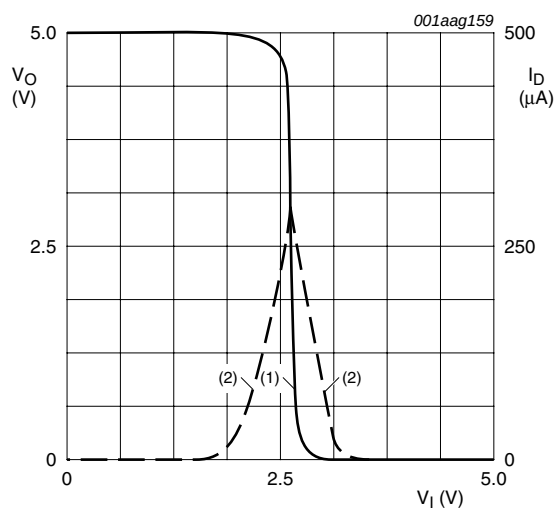
Definitions for test circuit:
 C_L = load capacitance including jig and probe capacitance;
 R_T = termination resistance should be equal to the output impedance Z_o of the pulse generator;
For test data refer to [Table 8](#).

Fig 5. Test circuit for measuring switching times

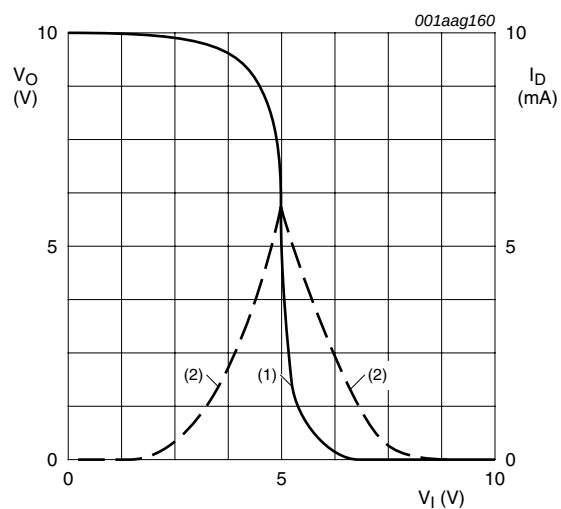
Table 8. Test data

Supply voltage	Input		Load
V_{DD}	V_I	t_r, t_f	C_L
5 V to 15 V	V_{SS} or V_{DD}	≤ 20 ns	50 pF

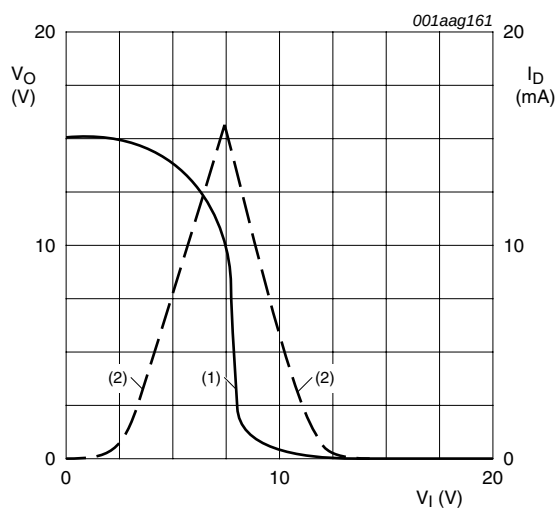
11.1 Transfer characteristics



a. $V_{DD} = 5\text{ V}$; $I_O = 0\text{ A}$



b. $V_{DD} = 10\text{ V}$; $I_O = 0\text{ A}$



c. $V_{DD} = 15\text{ V}$; $I_O = 0\text{ A}$

- (1) V_O = output voltage.
- (2) I_D = drain current.

Fig 6. Typical transfer characteristics

12. Application information

Some examples of applications for the HEF4069UB.

[Figure 7](#) shows an astable relaxation oscillator using two HEF4069UB inverters and 2 BAW62 diodes. The oscillation frequency is mainly determined by $R1 \times C1$, provided $R1 \ll R2$ and $R2 \times C2 \ll R1 \times C1$.

The function of $R2$ is to minimize the influence of the forward voltage across the protection diodes on the frequency; $C2$ is a stray (parasitic) capacitance.

The period T_p is given by $T_p = T_1 + T_2$,

where:

$$T_1 = R1C1 \ln \frac{V_{DD} + V_{ST}}{V_{ST}}$$

$$T_2 = R1C1 \ln \frac{2V_{DD} - V_{ST}}{V_{DD} - V_{ST}}$$

V_{ST} = the signal threshold level of the inverter.

The period is fairly independent of V_{DD} , V_{ST} and temperature. The duty factor, however, is influenced by V_{ST} .

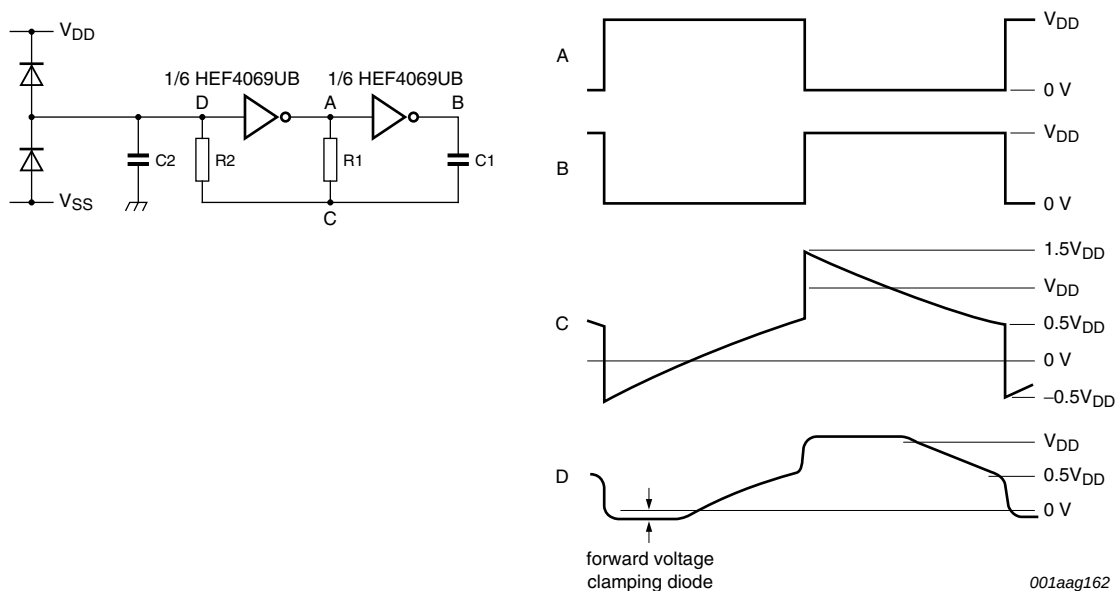
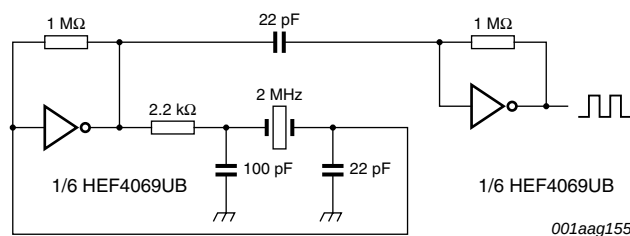


Fig 7. Astable relaxation oscillator

[Figure 8](#) shows a crystal oscillator for frequencies up to 10 MHz using two HEF4069UB inverters. The second inverter amplifies the oscillator output voltage to a level sufficient to drive other Local Oxidation CMOS (LOCMOS) circuits.



The output inverter is used to amplify the oscillator output voltage to a level sufficient to drive other LOCMOS circuits.

Fig 8. Crystal oscillator

[Figure 9](#) and [Figure 10](#) show voltage gain and supply current. [Figure 11](#) shows the test set-up and an example of an analog amplifier using one HEF4069UB.

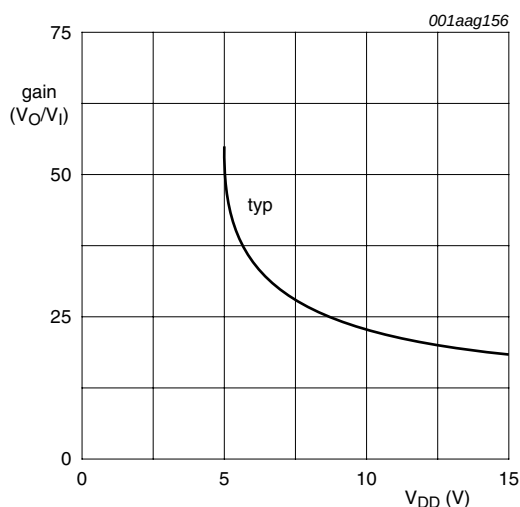


Fig 9. Typical voltage gain as a function of supply voltage

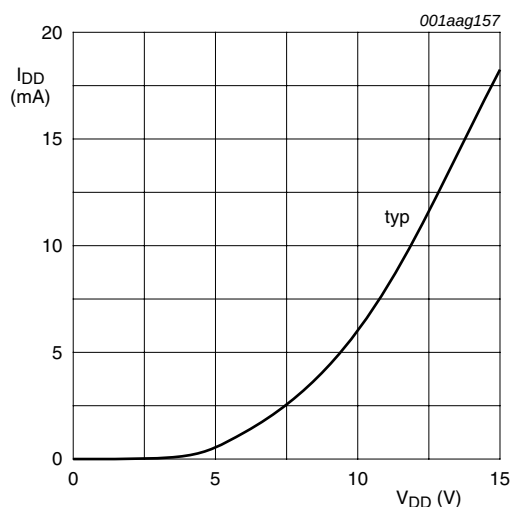


Fig 10. Typical supply current as a function of supply voltage

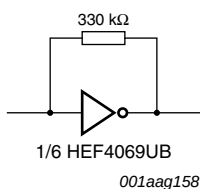
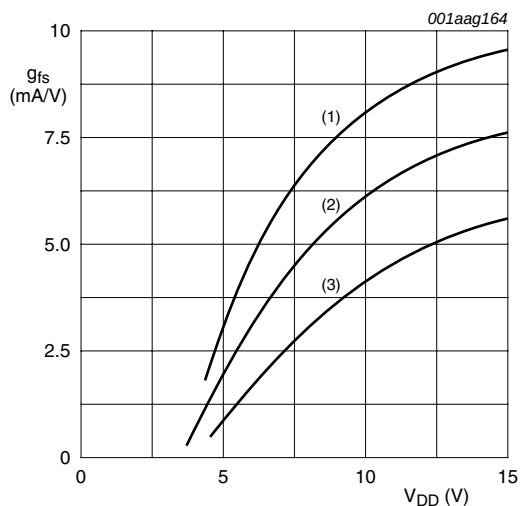


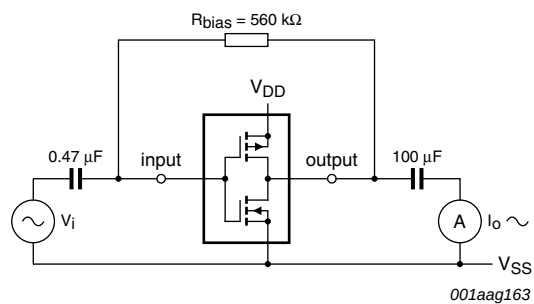
Fig 11. Test set-up

Figure 12 shows typical forward transconductance and Figure 13 shows the test set-up.



- (1) Average.
- (2) Average +2σ; where: 'σ' is the standard deviation.
- (3) Average -2σ; where: 'σ' is the standard deviation.

Fig 12. Typical forward transconductance as a function of supply voltage at $T_{amb} = 25\text{ °C}$



$$g_{fs} = \frac{dI_o}{dV_i} \text{ at } V_O \text{ is constant.}$$

$$f_i = 1 \text{ kHz}$$

Fig 13. Test set-up

13. Package outline

DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1

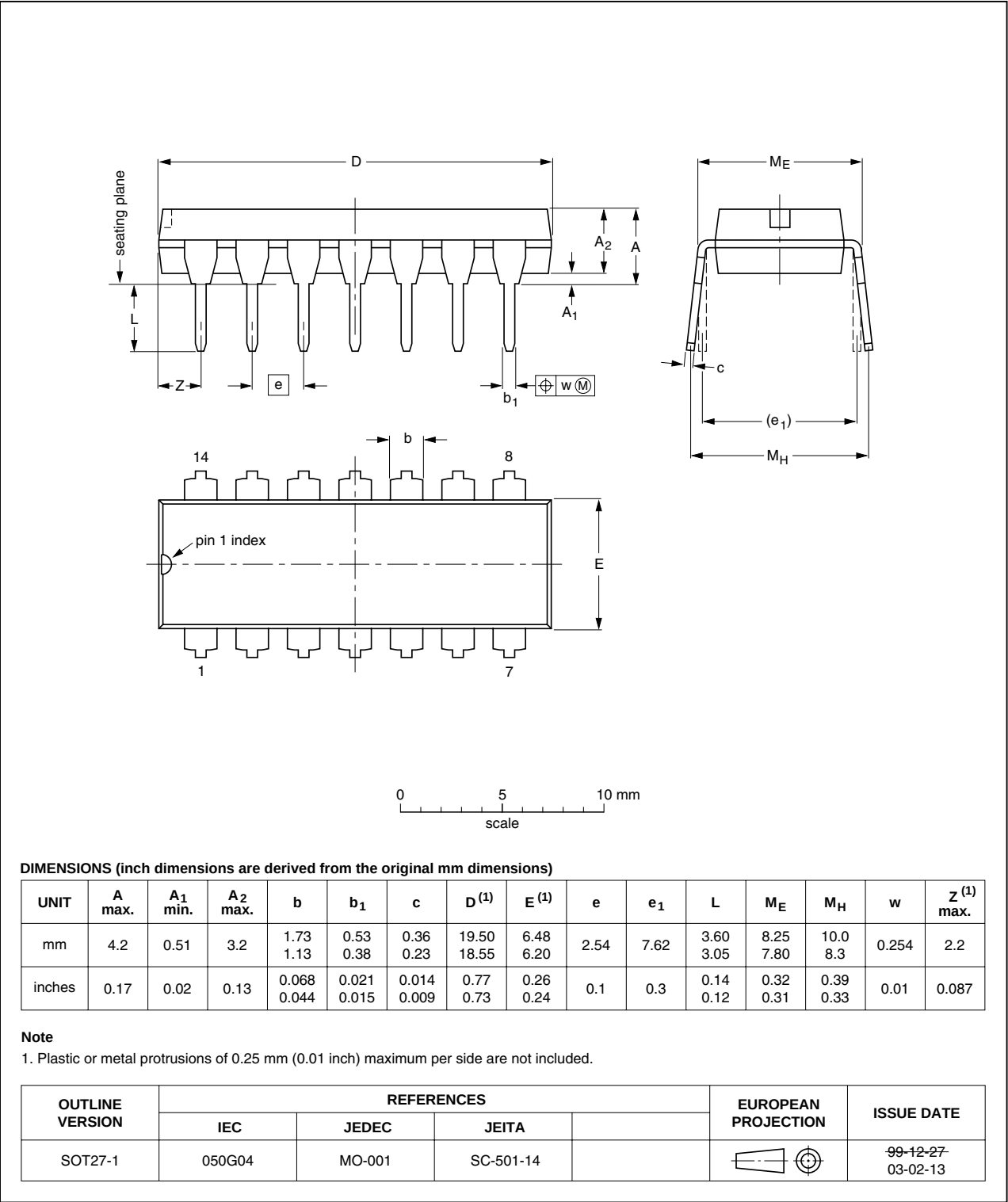


Fig 14. Package outline SOT27-1 (DIP14)

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1

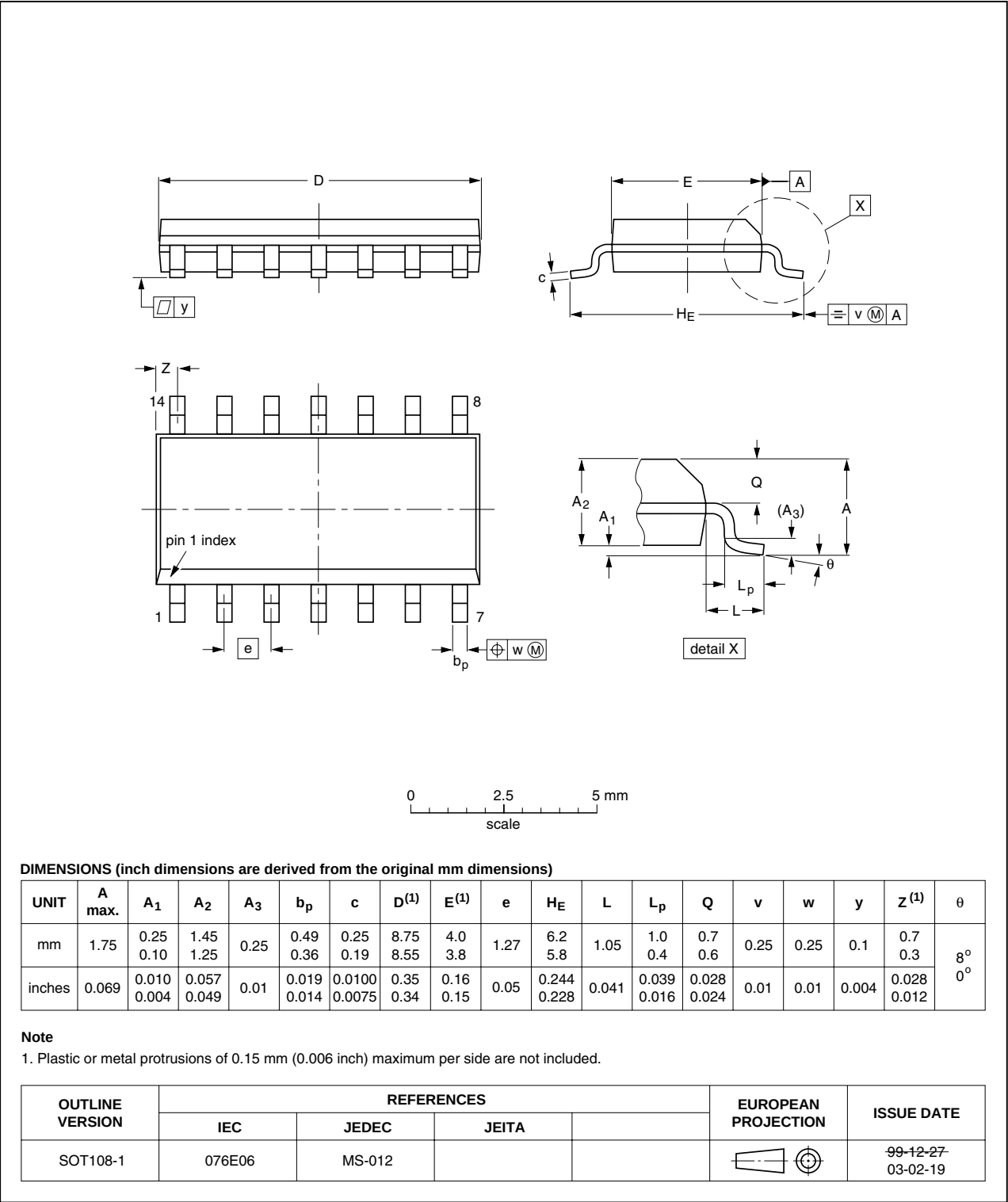


Fig 15. Package outline SOT108-1 (SO14)

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1

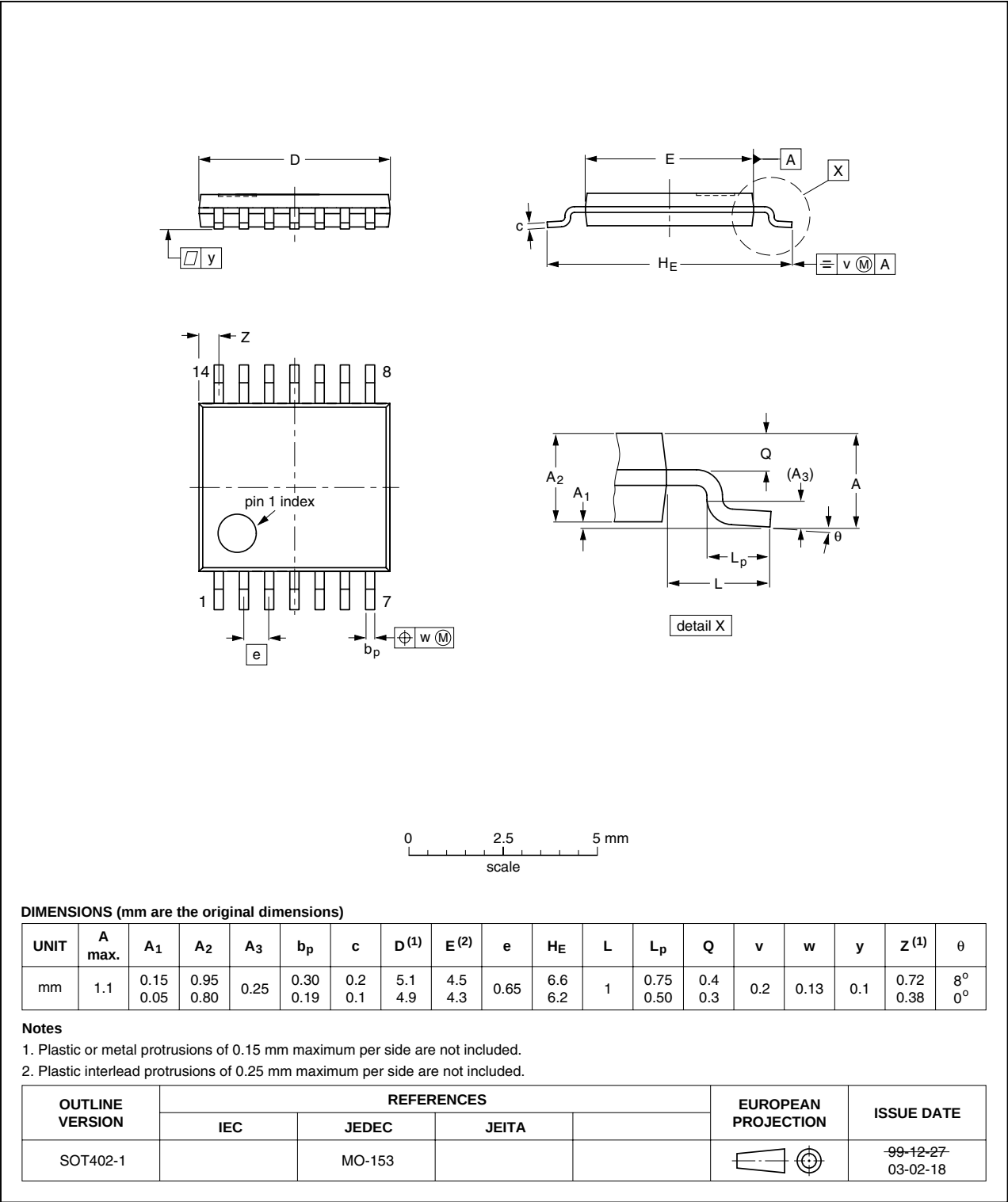


Fig 16. Package outline SOT402-1 (TSSOP14)

14. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF4069UB_6	20091208	Product data sheet	-	HEF4069UB_5
Modifications:	• Section 8 "Recommended operating conditions" $\Delta t/\Delta V$ values removed. • Section 12 "Application information" Figure 13 "Test set-up" updated. • Section 15 "Legal information" export control statement added.			
HEF4069UB_5	20090723	Product data sheet	-	HEF4069UB_4
HEF4069UB_4	20080704	Product data sheet	-	HEF4069UB_CNV_3
HEF4069UB_CNV_3	19950101	Product specification	-	HEF4069UB_CNV_2
HEF4069UB_CNV_2	19950101	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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